## **Supplementary Information**

## Chemical solution deposition of the highly *c*-axis oriented apatite type lanthanum silicate thin films

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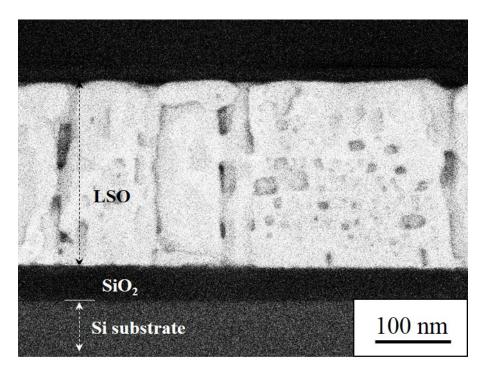


Figure S1 Cross-sectional backscattered electron images of the highly *c*-axis oriented LSO thin film.

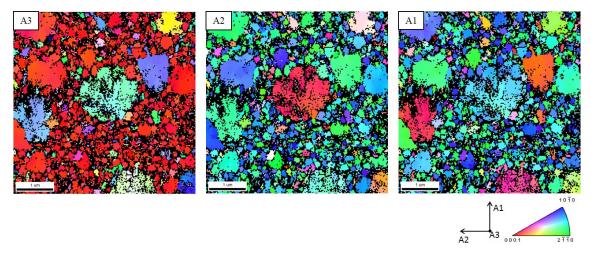


Figure S2 Inverse pole figure maps with different observation directions.

Each domain exhibited a single color for each direction, which suggests a tri-axial orientation.

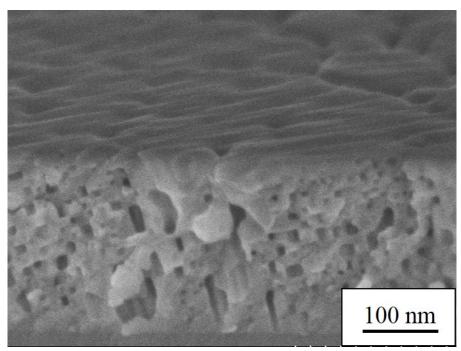
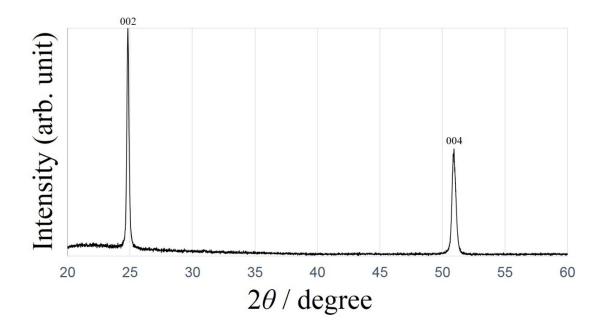
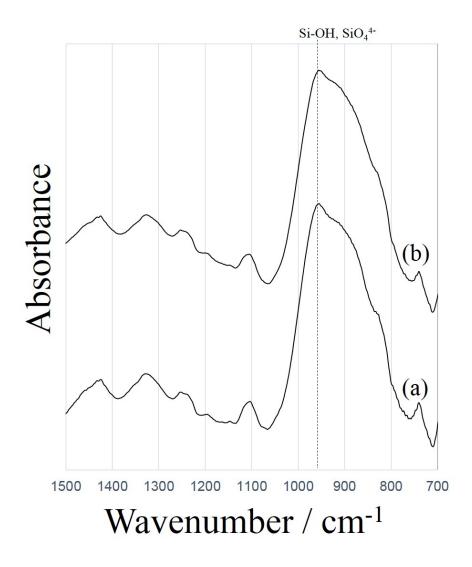


Figure S3 Diagonal cross section of the domain of the LSO thin film prepared from non-refluxed solution.



**Figure S4** XRD pattern for LSO thin film on a quartz glass substrate. The LSO thin film was obtained by the same procedure described in the experimental section using a non-refluxed solution.



**Figure S5** FT-IR spectra of the LSO thin films prepared from (a) refluxed and (b) non-refluxed solutions. Both spectra were measured by ATR-mode and normalized at the maximum peak marked by broken line.

Both spectra were identical each other. Because thermal decomposition of  $La(NO_3)_3$  is known to result in  $LaONO_3$  at 400°C,<sup>S1-S3</sup> broad two peaks from 1280 – 1500 cm<sup>-1</sup> can be attributed to lanthanum nitrate which shows the peaks at 1455, 1425, 1325, 1300 cm<sup>-1</sup>.<sup>S3</sup> Strong peak from 800 – 1050 cm<sup>-1</sup> is known to be related to Si-OH and SiO<sub>4</sub><sup>4-</sup>.<sup>S3</sup> Relative small siloxane (Si-O-Si) peak generally appears at ca. 1080 cm<sup>-1</sup> interestingly suggests that Si-O bonding state in LSO precursor thin films are mainly SiO<sub>4</sub><sup>4-</sup>. Other peaks at ca. 750, 1200, 1250 cm<sup>-1</sup> derived from Si substrate.

## References

S1 H. Tagawa, Yokohama-kokuritsudai Kankyoken Kiyo, 1987, 14, 41. (Written in Japanese)

- S2 S. Mentus, D. Jelić and V. Grudić, J. Therm. Anal. Calorim., 2007, 90, 393.
- S3 B. Ballinger, J. Motuzas, C. R. Miller, S. Smart and J. C. Diniz da Costa, *Scientific Reports*, 2015, 5, 8210